Abstract Submitted
for the MAR13 Meeting of
The American Physical Society

Quantumn Hall Effect in single-, bi- and tri-layer graphene ZENG ZHAO, KEVIN MYHRO, DAVID TRAN, HANG ZHANG, JHAO-WUN HUANG, JAIRO VELASCO, YANMENG SHI, FENGLIN WANG, YONGJIN LEE, CHUN NING LAU, University of California, Riverside — Quantum Hall Effect has been extensively studied in single layer, bilayer and trilayer graphene. Our recent studies showed intrinsic gapped state at the charge neutrality point in bilayer and trilayer graphene. Here we describe the fabrication of high-quality single-bilayer and bi-trilayer hybrid graphene devices, and present results from magneto-transport measurements.

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Date submitted: 28 Nov 2012 Electronic form version 1.4